

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0040] as follows:

[0040] Although the foregoing embodiments have been described with respect to Metal Semiconductor Field Effect Transistors (MESFETs), it is also possible to further provide an insulating layer (reference numerals 19 and 79 in Figs. 1 and 4, respectively) on the AlGaN layer to adopt Metal Insulator Semiconductor Field Effect Transistors (MISFETs). In the case of MISFETs, there is no possibility of occurrence of "gate leak" essentially. However, the problem of "parallel conduction" can be solved by the present invention as in the case of MESFETs.